

Description

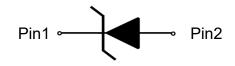
The XT3D5VU TVS diode is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebooks, and PDA's. It offers superior electrical characteristics such as low clamping voltage, low leakage current and high surge capability. It is designed to protect sensitive electronic components which are connected to power lines, from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lighting.

The XT3D5VU is in a SOD-323 package and will protect one unidirectional line. It may be used to provide ESD protection up to $\pm 30 \mathrm{kV}$ (Contact and air discharge) according to IEC61000-4-2 , and used to protect USB voltage bus pin (8/20 us) according to IEC61000-4-5.

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SOD-323



Circuit Diagram

Features

- ♦ Working voltage: 5V
- SOD323 Package
- ◆ 2000 Watts peak pulse power (t_p=8/20us)
- ◆ Transient protection for data lines to IEC 61000-4-2 (ESD) ±30kV (air),

 \pm 30kV (contact)

IEC 61000-4-5 (Surge) 110A (8/20us) IEC61000-4-4(EFT)40A(5/50ns)

- Low leakage current
- Low clamping voltage
- Solid-state silicon-avalanche technology

____5H____

Marking

Applications

- Power lines
- Personal digital assistants (PDA's)
- Microprocessors based equipment
- Notebooks, Desktops, and Servers
- ◆ Cell phone Handsets and Accessories
- Portable Electronics
- Peripherals

Order Information

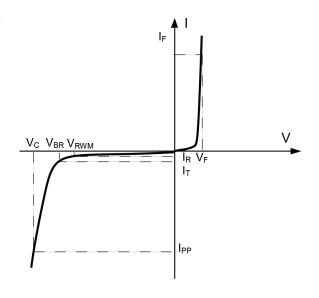
Device	Package	Shipping
XT3D5VU	SOD-323	3000/Tape&Reel

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Definitions of electrical characteristics

Symbol	Parameter	
V_{RWM}	Reverse Stand-off Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V_{BR}	Reverse Breakdown Voltage @ I⊤	
lτ	Test Current	
Ірр	Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
l _F	Forward Current	
VF	Forward Voltage @ I⊧	
C _j	Junction Capacitance	
Ірр	Peak Pulse Current	



Absolute Maximum Rating

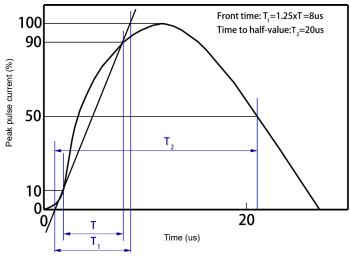
Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20μS)	Ррк	2000	W
ESD according to IEC61000-4-2 air discharge	V	±30	kV
ESD according to IEC61000-4-2 contact discharge	V _{ESD}	±30	kV
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	Тор	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

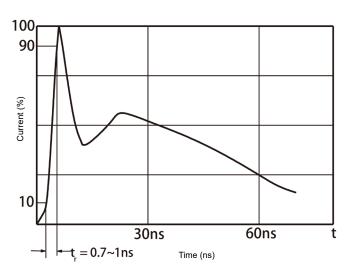
Electrical Characteristics (Ta=25℃, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				5	V
Reverse Breakdown Voltage	V_{BR}	I _T =1mA	6	7	8	V
Reverse Leakage Current	I _R	V _{RWM} =5V			1	μΑ
Peak Pulse Current	I _{PP}	t _P = 8/20μs			110	Α
Clamping Voltage	Vc	I _{PP} =50A t _P = 8/20μs		11	13	V
Clamping Voltage	Vc	I _{PP} =110A t _P = 8/20μs		14	17	V
Junction Capacitance	Cj	V _R =0V f = 1MHz	900	980	1050	pF



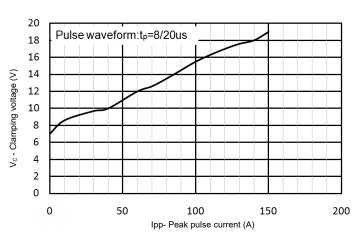
Typical Characteristics (Ta=25℃, unless otherwise noted)

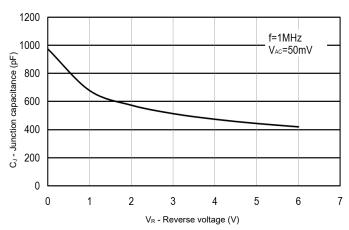




8/20 us waveform per IEC61000-4-5

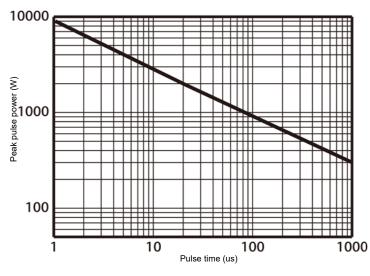
Contact discharge current waveform per IEC61000-4-2

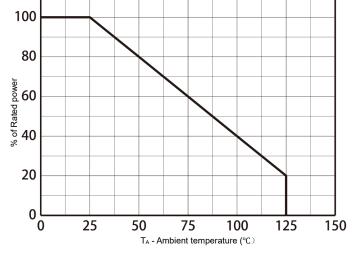




Clamping voltage vs. Peak pulse current

Capacitance vs. Reverse voltage



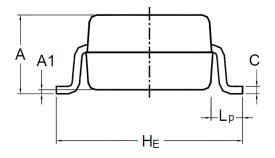


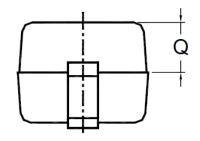
Non-repetitive peak pulse power vs. Pulse time

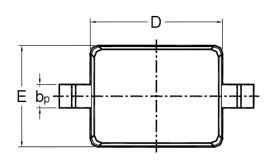
Power derating vs. Ambient temperature



Package Outline Dimensions (SOD-323)

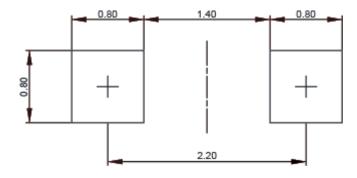






Dim	Inches		Millimeters	
	MIN	MAX	MIN	MAX
А	0.031	0.043	0.8	1.0
A ₁	0.000	0.004	0	0.1
bp	0.010	0.016	0.25	0.4
С	0.000	0.006	0	0.15
D	0.063	0.071	1.6	1.8
E	0.045	0.053	1.15	1.35
HE	0.091	0.110	2.3	2.8
L _P	0.004	0.020	0.1	0.5
Q	0.012	0.020	0.3	0.5

Recommend Land Pattern (Unit: mm)

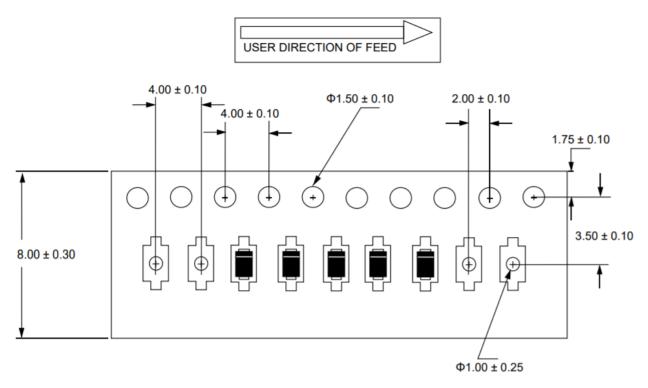


Note:

This recommended land pattern is for reference purpose only.



Load With Information



Unit: mm

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